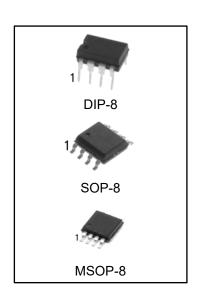


TLC5615 10-BIT DIGITAL-TO-ANALOG CONVERTERS

Features

- 10-Bit CMOS Voltage Output DAC in an 8-Terminal Package
- 5V Single Supply Operation
- 3-Wire Serial Interface
- High-Impedance Reference Inputs
- Voltage Output Range:2 Times the Reference Input Voltage
- Internal Power-On Reset
- Low Power Consumption:1.75mW(Max)
- Update Rate of 1.21 MHz
- Settling Time to 0.5 LSB:12.5 μs(Typ)
- Monotonic Over Temperature
- Pin Compatible With the Maxim MAX515



Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
TLC5615IN	DIP-8	C5615I	TUBE	2000pcs/box
TLC5615CN	DIP-8	C5615C	TUBE	2000pcs/box
TLC5615IM/TR	SOP-8	C5615I	REEL	2500pcs/reel
TLC5615CM/TR	SOP-8	C5615C	REEL	2500pcs/reel
TLC5615IMM/TR	MSOP-8	C5615I	REEL	3000pcs/reel
TLC5615CMM/TR	MSOP-8	C5615C	REEL	3000pcs/reel



Description

The TLC5615 is a 10-bit voltage output digital-to-analog converter (DAC) with a buffered reference input (high impedance). The DAC has an output voltage range that is two times the reference voltage, and the DAC is monotonic. The device is simple to use, running from a single supply of 5 V. A power-on-reset function is incorporated to ensure repeatable start-up conditions.

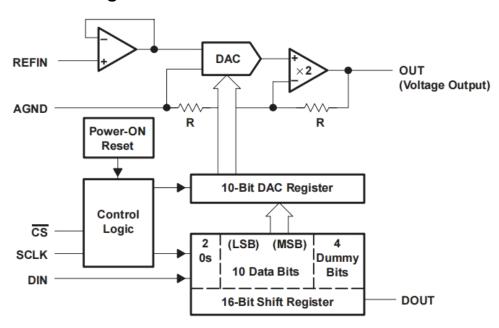
Digital control of the TLC5615 is over a three-wire serial bus that is CMOS compatible and easily interfaced to industry standard microprocessor and micro controller devices. The device receives a 16-bit data word to produce the analog output. The digital inputs feature Schmitt triggers for high noise immunity. Digital communication protocols include the SPITM, QSPITM, and MicrowireTM standards.

The 8-terminal small-outline D package allows digital control of analog functions in space-critical applications. The TLC5615C is characterized for operation from 0°C to 70°C. The TLC5615I is characterized for operation from -40°C to 85°C.

Applications

- Battery-Powered Test Instruments
- Digital Offset and Gain Adjustment
- Battery Operated/Remote Industrial Controls
- Machine and Motion Control Devices
- Cellular Telephones

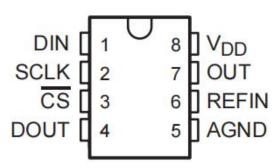
Functional block diagram





Pin Configuration

DIP-8/SOP-8/MSOP-8



Terminal Functions

TERMI NAME	NAL NO.	I/O	DESCRIPTION
DIN	1	I	Serial data input
SCLK	2	I	Serial clock input
CS	3	I	Chip select, active low
DOUT	4	0	Serial data output for daisy chaining
AGND	5		Analog ground
REFIN	6	I	Reference input
OUT	7	0	DAC analog voltage output
V _{DD}	8		Positive power supply



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Condition		Min	Max	
Supply voltage (VDD to AGND)		-	7 V	
Digital input voltage range to AGND		- 0.3 V	VDD + 0.3 V	
Reference input voltage range to AGND		-0.3 V	VDD + 0.3 V	
Output voltage at OUT from extrnal source		-	VDD + 0.3 V	
Continuous current at any terminal		-20mA	+20mA	
	TLC5615C	0°C	70°C	
Operating free-air temperature range,TA:	TLC5615I	-40°C	85 °⊂	
Storage temperature range, T _{Stg}		-65°C	150 °C	
Lead Temperature (Soldering, 10 seconds)		-	245 °ℂ	

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability

Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
Supply voltage, VDD		4.5	5	5.5	V
High-level digital input voltage, VIH		2.4			V
Low-level digital input voltage, VIL				8.0	V
Reference voltage, Vref to REFIN term	ninal	2	2.048 V _{DD} -2		V
Load resistance, RL		2			kΩ
0 1 1 1 1 1	TLC5615C	0		70	$^{\circ}\mathbb{C}$
Operating free-air temperature, TA	TLC5615I	-40		85	$^{\circ}\mathbb{C}$

Electrical Characteristics

over recommended operating free-air temperature range, V_{DD} = 5 V ±5%, Vref = 2.048 V (unless otherwise noted) static DAC specifications

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			10			bits
Integral nonlinearity, end point adjus	ted (INL)	V _{ref} = 2.048 V,See Note 1			±1	LSB
Differential nonlinearity (DNL)		V _{ref} = 2.048 V,See Note 2		±0.1	±0.5	LSB
Zero-scale error (offset error at zero		V 6 0.040 V 0 Note 0			±3	LSB
scale)		V _{ref} = 2.048 V,See Note 3				
Zero-scale-error temperature coeffic	ient	V _{ref} = 2.048 V,See Note 4		3		ppm/℃
EG Gain error		V _{ref} = 2.048 V,See Note 5			±3	LSB
Gain-error temperature coefficient		V _{ref} = 2.048 V,See Note 6		1		ppm/℃
	Zero scale	0 11 7 10	80			
PSRR Power-supply rejection ratio	Gain	See Notes 7 and 8	80			dB
Analog full scale output		R _L = 100 kΩ	2V _r	ef(1023/10)24)	V



- The relative accuracy or integral nonlinearity (INL), sometimes referred to as linearity error, is the maximum deviation of the output from the line between zero and full scale excluding the effects of zero code and full-scale errors (see text).
- The differential nonlinearity (DNL), sometimes referred to as differential error, is the difference between the measured and ideal 1 LSB amplitude change of any two adjacent codes. Monotonic means the output voltage changes in the same direction (or remains constant) as a change in the digital input code.
- 3. Zero-scale error is the deviation from zero-voltage output when the digital input code is zero (see text).
- Zero-scale-error temperature coefficient is given by:
 EZS TC = [EZS (Tmax) EZS (Tmin)]/Vref ×10⁶/(Tmax Tmin).
- 5. Gain error is the deviation from the ideal output (Vref 1 LSB) with an output load of 10 kΩ excluding the effects of the zero-scale error.
- 6. Gain temperature coefficient is given by: EG TC = [EG(Tmax) EG (Tmin)]/Vref ×10⁶/(Tmax Tmin).
- Zero-scale-error rejection ratio (EZS-RR) is measured by varying the VDD from 4.5 V to 5.5 V dc and measuring the proportion of this signal imposed on the zero-code output voltage.
- 8. Gain-error rejection ratio (EG-RR) is measured by varying the VDD from 4.5 V to 5.5 V dc and measuring the proportion of this signal imposed on the full-scale output voltage after subtracting the zero-scale change.

Voltage Output (Out)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vo	Voltage output range	R _L = 10 kΩ	0		V _{DD} -0.4	V
	Output load regulation accuracy	$VO(OUT) = 2 V_{RL} = 2 k\Omega$			0.5	LSB
losc	Output short circuit current	OUT to VDD or AGND		20		mA
VOL(low)	Output voltage, low-level	IO(OUT) ≤ 5 mA			0.25	V
VOH(high)	Output voltage, high-level	IO(OUT) ≤ -5 mA	4.75			V

Electrical Characteristics

over recommended operating free-air temperature range, V_{DD} = 5 V ± 5%, Vref = 2.048 V (unless otherwise noted) (continued) reference input (REFIN)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VI	Input voltage		0	\	V _{DD} -2	V
rį	Input resistance		10			ΜΩ
Ci	Input capacitance		5			pF

digital inputs (DIN, SCLK, CS)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIH	High-level digital input voltage		2.4			V
VIL	Low-level digital input voltage				0.8	V
۱н	High-level digital input current	VI = VDD			±1	μA
ΙΙL	Low-level digital input current	V _I = 0			±1	μA
Ci	Input capacitance		8			pF

digital output (DOUT)

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
VOH Output voltage, high-level	I _O = -2 mA	V _{DD} –1		V
VOL Output voltage, low-level	IO = 2 mA		0.4	V



power supply

PARAMETER	TEST CONDIT	TONS	MIN	TYP	MAX	UNIT
V _{DD} Supply voltage			4.5	5	5.5	V
	V _{DD} = 5.5 V,					
	No load,	Vref = 0		150	250	μA
IDD Davies averally average	All inputs = 0 V or VDD					
IDD Power supply current	V _{DD} = 5.5 V,					
	No load,	V _{ref} = 2.048 V		230	350	μA
	All inputs = 0 V or VDD					

analog output dynamic performance

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Signal-to-noise + distortion, S/(N+D)	V _{ref} = 1 V _{pp} at 1 kHz + 2.048 Vdc, code = 11 1111 1111, See Note 9	60			dB

NOTE 9: The limiting frequency value at 1 Vpp is determined by the output-amplifier slew rate.

digital input timing requirements (see Figure 1)

	PARAMETER	MIN	TYP	MAX	UNIT
t _{su(DS)}	Setup time, DIN before SCLK high	45			ns
th(DH)	Hold time, DIN valid after SCLK high	0			ns
t _{su(CSS)}	Setup time, $\overline{\text{CS}}$ low to SCLK high	1			ns
tsu(CS1)	Setup time, $\overline{\text{CS}}$ high to SCLK high	50			ns
th(CSH0)	Hold time, SCLK low to $\overline{\text{CS}}$ low	1			ns
th(CSH1)	Hold time, SCLK low to $\overline{\text{CS}}$ high	0			ns
tw(CS)	Pulse duration, minimum chip select pulse width high	20			ns
tw(CL)	Pulse duration, SCLK low	25			ns
tw(CH)	Pulse duration, SCLK high	25			ns

output switching characteristic

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tpd(DOUT) Propagation delay time, DOUT	CL = 50 pF			50	ns



Operating Characteristics

over recommended operating free-air temperature range, V_{DD} = 5 V ±5%, Vref = 2.048 V (unless otherwise noted) analog output dynamic performance

	PARAMETER	TEST C	MIN	TYP	MAX	UNIT				
SR	Output slew rate	C _L = 100 pF,T _A = 25°C	$R_L = 10 \text{ k}\Omega$	0.3	0.5		V/µs			
ts	Output settling time	To 0.5 LSB,R _L = 10 kΩ,	C _L = 100 pF, See Note 10		12.5		μs			
Glitch energy		DIN = All 0s to all 1s			5		Nv•s			

NOTE 10: Settling time is the time for the output signal to remain within ± 0.5 LSB of the final measured value for a digital input code change of 000 hex to 3FF hex or 3FF hex to 000 hex.

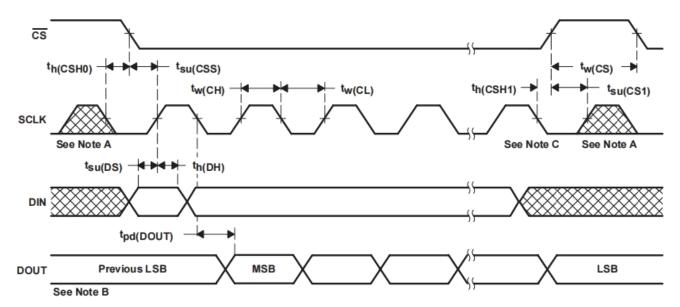
reference input (REFIN)

PARAMETER	TEST CO	MIN	TYP	MAX	UNIT	
Reference feedthrough	REFIN = 1 V _{pp} at 1 kHz +		-80		dB	
Reference input bandwidth (f–3dB)	REFIN = 0.2 V _{pp} + 2.048 Vdc	REFIN = 0.2 V _{pp} + 2.048		30		kHz

NOTE 11: Reference feed through is measured at the DAC output with an input code = 000 hex and a Vref input = 2.048 Vdc + 1 Vpp at 1 kHz.



Parameter Measurement Information

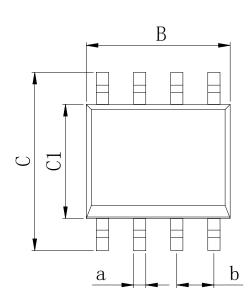


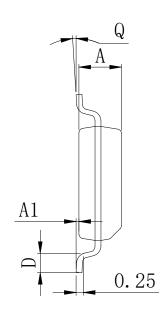
- A. The input clock, applied at the SCLK terminal, should be inhibited low when CS is high to minimize clock feedthrough.
- B. Data input from preceeding conversion cycle.
- C. Sixteenth SCLK falling edge



Physical Dimensions

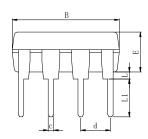
SOP-8



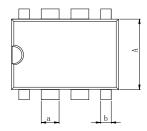


Dimensions In M	Dimensions In Millimeters(SOP-8)											
Symbol:	Α	A1	В	С	C1	D	Q	а	b			
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	1.27 BSC			
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	1.21 000			

DIP-8





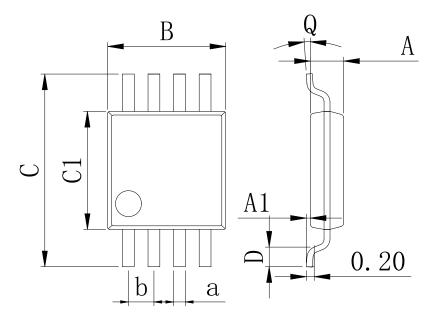


Dimensions In Millimeters(DIP-8)											
Symbol:	Α	В	D	D1	Е	L	L1	а	b	С	d
Min:	6.10	9.00	8.10	7.42	3.10	0.50	3.00	1.50	0.85	0.40	2.54 BSC
Max:	6.68	9.50	10.9	7.82	3.55	0.70	3.60	1.55	0.90	0.50	



Physical Dimensions

MSOP-8



Dimensions In M	Dimensions In Millimeters(MSOP-8)											
Symbol:	Α	A1	В	С	C1	D	Q	а	b			
Min:	0.80	0.05	2.90	4.75	2.90	0.35	0°	0.25	0.65 BSC			
Max:	0.90	0.20	3.10	5.05	3.10	0.75	8°	0.35				



Revision History

DATE	REVISION	PAGE
2015-8-9	New	1-12
2023-8-26	Update encapsulation type . Update Lead Temperature . Updated DIP-8 dimension	1、4、9



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